Jamie D Phillips

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157 papers	3,926 citations	33 h-index	57 g-index
180 ext. papers	4,446 ext. citations	3 avg, IF	5.41 L-index

#	Paper	IF	Citations
157	Evaluation of the fundamental properties of quantum dot infrared detectors. *Journal of Applied Physics*, **2002**, 91, 4590-4594	2.5	214
156	Far-infrared photoconductivity in self-organized InAs quantum dots. *Applied Physics Letters*, **1998**, 72, 2020-2022	3.4	209
155	Self-assembled InAs-GaAs quantum-dot intersubband detectors. *IEEE Journal of Quantum Electronics*, **1999**, 35, 936-943	2	182
154	Room-temperature operation of In0.4Ga0.6As/GaAs self-organised quantum dot lasers. *Electronics Letters*, **1996**, 32, 1374	1.1	182
153	Intermediate-band photovoltaic solar cell based on ZnTe:O. *Applied Physics Letters*, **2009**, 95, 011103	3.4	168
152	Sub-bandgap photoconductivity in ZnO epilayers and extraction of trap density spectra. *Semiconductor Science and Technology*, **2006**, 21, 717-723	1.8	124
151	Absorption, carrier lifetime, and gain in InAs-GaAs quantum-dot infrared photodetectors. *IEEE Journal of Quantum Electronics*, **2003**, 39, 459-467	2	118
150	ZnO thin-film transistors with polycrystalline (Ba,Sr)TiO3 gate insulators. *Applied Physics Letters*, **2006**, 88, 212903	3.4	91
149	Mid-wave infrared HgCdTe nBn photodetector. *Applied Physics Letters*, **2012**, 100, 161102	3.4	86
148	Optimization of random diffraction gratings in thin-film solar cells using genetic algorithms. *Solar Energy Materials and Solar Cells*, **2008**, 92, 1689-1696	6.4	81
147	In(Ga)As/GaAs self-organized quantum dot lasers: DC and small-signal modulation properties. *IEEE Transactions on Electron Devices*, **1999**, 46, 871-883	2.9	81
146	Small-signal modulation and differential gain of single-mode self-organized In0.4Ga0.6As/GaAs quantum dot lasers. *Applied Physics Letters*, **1997**, 70, 2952-2953	3.4	75
145	Nanometer-scale studies of vertical organization and evolution of stacked self-assembled InAs/GaAs quantum dots. *Applied Physics Letters*, **1999**, 74, 2824-2826	3.4	71
144	Photoluminescence and far-infrared absorption in Si-doped self-organized InAs quantum dots. *Applied Physics Letters*, **1997**, 71, 2079-2081	3.4	70
143	Self-organized In0.4Ga0.6As quantum-dot lasers grown on Si substrates. *Applied Physics Letters*, **1999**, 74, 1355-1357	3.4	70
142	A new class of room-temperature multiferroic thin films with bismuth-based supercell structure. *Advanced Materials*, **2013**, 25, 1028-32	24	66
141	Trap-related photoconductivity in ZnO epilayers. *Journal of Electronic Materials*, **2006**, 35, 543-549	1.9	66

140	Drift-Diffusion Modeling for Impurity Photovoltaic Devices. *IEEE Transactions on Electron Devices*, **2009**, 56, 3168-3174	2.9	62
139	AlGaAs Photovoltaics for Indoor Energy Harvesting in mm-Scale Wireless Sensor Nodes. *IEEE Transactions on Electron Devices*, **2015**, 62, 2170-2175	2.9	56
138	Interdiffusion and surface segregation in stacked self-assembled InAs/GaAs quantum dots. *Applied Physics Letters*, **1999**, 75, 2797-2799	3.4	56
137	Model for intermediate band solar cells incorporating carrier transport and recombination. *Journal of Applied Physics*, **2009**, 105, 064512	2.5	54
136	Growth and structural properties of m-plane ZnO on MgO (001) by molecular beam epitaxy. *Applied Physics Letters*, **2008**, 92, 233505	3.4	50
135	Design and Modeling of HgCdTe nBn Detectors. *Journal of Electronic Materials*, **2011**, 40, 1624-1629	1.9	47
134	Generation and recombination rates at ZnTe:O intermediate band states. *Applied Physics Letters*, **2009**, 95, 261107	3.4	47
133	Subcutaneous Photovoltaic Infrared Energy Harvesting for Bio-Implantable Devices. *IEEE Transactions on Electron Devices*, **2017**, 64, 2432-2437	2.9	46
132	Hysteretic metal□ferroelectric□semiconductor capacitors based on PZT/ZnO heterostructures. *Journal Physics D: Applied Physics*, **2007**, 40, 2430-2434	3	43
131	Energy Harvesting for GaAs Photovoltaics Under Low-Flux Indoor Lighting Conditions. *IEEE Transactions on Electron Devices*, **2016**, 63, 2820-2825	2.9	39
130	Gain dynamics and ultrafast spectral hole burning in In(Ga)As self-organized quantum dots. *Applied Physics Letters*, **2002**, 81, 670-672	3.4	38
129	Design of an Auger-Suppressed Unipolar HgCdTe NB□N Photodetector. *Journal of Electronic Materials*, **2012**, 41, 2886-2892	1.9	35
128	Predicted Performance Improvement of Auger-Suppressed HgCdTe Photodiodes and $phbox{-}n$ Heterojunction Detectors. *IEEE Transactions on Electron Devices*, **2011**, 58, 501-507	2.9	34
127	Optical Characteristics of ZnTeO Thin Films Synthesized by Pulsed Laser Deposition and Molecular Beam Epitaxy. *Journal of Electronic Materials*, **2009**, 38, 119-125	1.9	34
126	A DC Voltage Dependant Switchable Thin Film Bulk Wave Acoustic Resonator Using Ferroelectric Thin Film. *IEEE MTT-S International Microwave Symposium Digest IEEE MTT-S International Microwave Symposium*, **2007**,		34
125	Detailed study of above bandgap optical absorption in HgCdTe. *Journal of Electronic Materials*, **2005**, 34, 773-778	1.9	34
124	Thermal emission in type-II GaSb/GaAs quantum dots and prospects for intermediate band solar energy conversion. *Journal of Applied Physics*, **2012**, 111, 074514	2.5	33
123	Characteristics of InAs/AlGaAs self-organized quantum dot modulation doped field effect transistors. *Applied Physics Letters*, **1998**, 72, 3509-3511	3.4	32

122	Linear and quadratic electro-optic coefficients of self-organized In0.4Ga0.6As/GaAs quantum dots. *Applied Physics Letters*, **1998**, 72, 1275-1277	3.4	31
121	Bistability and self-pulsation in quantum-dot lasers with intracavity quantum-dot saturable absorbers. *Applied Physics Letters*, **1999**, 74, 1654-1656	3.4	31
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119	An Intrinsically Switchable FBAR Filter Based on Barium Titanate Thin Films. *IEEE Microwave and Wireless Components Letters*, **2009**, 19, 359-361	2.6	28
118	The disintegration of GaSb/GaAs nanostructures upon capping. *Applied Physics Letters*, **2013**, 102, 113103	3.4	26
117	Multiphoton Sub-Band-Gap Photoconductivity and Critical Transition Temperature in Type-II GaSb Quantum-Dot Intermediate-Band Solar Cells. *Physical Review Applied*, **2014**, 1,	4.3	25
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110	Electronic properties of ferroelectric BaTiO3□MgO capacitors on GaAs. *Applied Physics Letters*, **2004**, 85, 3208-3210	3.4	23
109	Normal incidence narrowband transmission filtering capabilities using symmetry-protected modes of a subwavelength, dielectric grating. *Optics Letters*, **2015**, 40, 2637-40	3	22
108	Intrinsically switchable, high-Q ferroelectricon-silicon composite film bulk acoustic resonators. *IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control*, **2014**, 61, 231-8	3.2	22
107	Analysis of the intermediate-band absorption properties of type-II GaSb/GaAs quantum-dot photovoltaics. *Physical Review B*, **2017**, 96,	3.3	22
106	ZnO/ZnSe/ZnTe Heterojunctions for ZnTe-Based Solar Cells. *Journal of Electronic Materials*, **2011**, 40, 1674-1678	1.9	22
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102	Complementary Thin-Film Electronics Based on n-Channel ZnO and p-Channel ZnTe. *IEEE Electron Device Letters*, **2009**, 30, 1314-1316	4.4	20
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82	Electric field dependence of piezoelectric coefficient in ferroelectric thin films. *Journal of Electroceramics*, **2006**, 17, 613-617	1.5	12
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80	Uniformity of optical absorption in HgCdTe epilayer measured by infrared spectromicroscopy. *Applied Physics Letters*, **2003**, 83, 3701-3703	3.4	12
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74	Optical waveguiding in BaTiO3▯MgO▯lxOy▯aAs heterostructures. *Applied Physics Letters*, **2004**, 85, 5206-5208	3.4	10
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68	Long-wavelength infrared transmission filters via two-step subwavelength dielectric gratings. *Optics Letters*, **2017**, 42, 518-521	3	8
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66	Arsenic Diffusion Study in HgCdTe for Low p-Type Doping in Auger-Suppressed Photodiodes. *Journal of Electronic Materials*, **2010**, 39, 945-950	1.9	8
65	Epitaxial growth and surface modeling of ZnO on c-plane Al2O3. *Applied Physics Letters*, **2004**, 85, 6338-6340	3.4	8
64	Polarization-independent narrowband transmittance filters via symmetry-protected modes in high contrast gratings. *Optics Letters*, **2020**, 45, 4348-4351	3	8
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60	Electrical Characteristics of PEDOT:PSS Organic Contacts to HgCdTe. *Journal of Electronic Materials*, **2007**, 36, 841-845	1.9	7
59	A 179-Lux Energy-Autonomous Fully-Encapsulated 17-mm3 Sensor Node with Initial Charge Delay Circuit for Battery Protection **2018**,		7
58	Surface morphology and straight crack generation of ultrafast laser irradiated □Ga2O3. *Journal of Applied Physics*, **2019**, 125, 223104	2.5	6
57	Chemical epitaxy and interfacial reactivity in solution deposited PbS on ZnTe. *Journal of Materials Chemistry C*, **2016**, 4, 1996-2002	7.1	6
56	Bridging the"Last Millimeter" Gap of Brain-Machine Interfaces via Near-Infrared Wireless Power Transfer and Data Communications. *ACS Photonics*, **2021**, 8, 1430-1438	6.3	6
55	Dual color longwave InAs/GaSb type-II strained layer superlattice detectors. *Infrared Physics and Technology*, **2015**, 70, 93-98	2.7	5
54	Intrinsically Switchable Ferroelectric Contour Mode Resonators. *IEEE Transactions on Microwave Theory and Techniques*, **2013**, 61, 2806-2813	4.1	5
53	Infrared Energy Harvesting in Millimeter-Scale GaAs Photovoltaics. *IEEE Transactions on Electron Devices*, **2017**, 64, 4554-4560	2.9	5
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49	Illumination instabilities in ZnO/HfO2 thin-film transistors and influence of grain boundary charge. *Journal of Materials Research*, **2012**, 27, 2199-2204	2.5	5
48	Intrinsically switchable contour mode acoustic wave resonators based on barium titanate thin films **2009**,		5
47	Temperature-dependent photoluminescence of In0.5Al0.5As/Al0.25Ga0.75As self-organized quantum dots. *Journal of Applied Physics*, **1999**, 85, 2997-2999	2.5	5
46	Heterojunction Band Offset Limitations on Open-Circuit Voltage in p-ZnT e/n-ZnSe Solar Cells. *IEEE Journal of Photovoltaics*, **2015**, 5, 874-877	3.7	4
45	Low damage electrical modification of 4H-SiC via ultrafast laser irradiation. *Journal of Applied Physics*, **2018**, 123, 145106	2.5	4
44	InGaAs/GaAsSb Type-II Superlattices for Short-Wavelength Infrared Detection. *Journal of Electronic Materials*, **2019**, 48, 6025-6029	1.9	4
43	Resolving spectral overlap issue of intermediate band solar cells using non-uniform sub-bandgap state filling. *Progress in Photovoltaics: Research and Applications*, **2014**, 22, 1062-1069	6.8	4
42	Oxygen Incorporation in ZnTeO Alloys via Molecular Beam Epitaxy. *Journal of Electronic Materials*, **2014**, 43, 889-893	1.9	4
41	Preserving voltage and long wavelength photoresponse in GaSb/GaAs quantum dot solar cells **2013**,		4
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37	Charge trapping and recovery in ALD HfO2/Ga2O3 (010) MOS capacitors. *Semiconductor Science and Technology*, **2021**, 36, 04LT01	1.8	4
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35	Passivation of long-wave infrared InAs/GaSb superlattice detectors with epitaxially grown ZnTe **2014**,		3
34	Growth and electroluminescent properties of self-organized In0.4Ga0.6As/GaAs quantum dots grown on silicon. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1999**, 17, 1116		3
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32	Conduction band offsets in CdZnSSe/ZnSSe single quantum wells measured by deep level transient spectroscopy. *Applied Physics Letters*, **1996**, 68, 3591-3593	3.4	3
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29	The effect of doping on low temperature growth of high quality GaAs nanowires on polycrystalline films. *Nanotechnology*, **2016**, 27, 495605	3.4	3
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26	Exploring new active regions for type I InAsSb strained-layer lasers. *Journal of Electronic Materials*, **2000**, 29, 91-93	1.9	2
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23	A Light-Tolerant Wireless Neural Recording IC for Motor Prediction With Near-Infrared-Based Power and Data Telemetry. *IEEE Journal of Solid-State Circuits*, **2022**, 1-1	5.5	2
22	Effects of high temperature annealing on the atomic layer deposited HfO2/Ga2O3 (010) interface. *Journal of Applied Physics*, **2022**, 131, 035106	2.5	2
21	Mid-wave infrared filtering in silicon subwavelength zero-contrast gratings **2020**,		2
20	Mid-wave infrared transmittance filters in suspended GaAs subwavelength gratings. *Applied Physics Letters*, **2021**, 119, 031103	3.4	2
19	Influence of Subwavelength Grating Asymmetry on Long-Wavelength Infrared Transmittance Filters. *IEEE Photonics Journal*, **2018**, 10, 1-8	1.8	2
18	Analysis of Carrier Transport in n-Type Hg1CdxTe with Ultra-Low Doping Concentration. *Journal of Electronic Materials*, **2018**, 47, 5699-5704	1.9	1
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16	ZnO nanorods for simultaneous light trapping and transparent electrode application in solar cells **2011**,		1
15	Decoupling spectral overlap of intermediate band solar cells using low-high state filling **2012**,		1

14	Room temperature self-organized quantum dot transistors		1
13	Far infrared modulated photoluminescence in InSb quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 22, 598-602	3	1
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11	High-speed modulation of quantum-dot lasers **1999**,		1
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9	Carrier dynamics of intermediate sub-bandgap transitions in ZnTeO. *Journal of Applied Physics*, **2019**, 126, 135701	2.5	0
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1	Tracking the Migration of the Monarch Butterflies with the WorldQs Smallest Computer. *GetMobile (New York, N Y)*, **2022**, 26, 25-29	0.8	